\* R3134K (DFN(PL)1212-6) and R3134Q (SC-88A) are the discontinued products as of March, 2016.



# R3134x SERIES

# LOW VOLTAGE DETECTOR WITH BUILT-IN DELAY CIRCUIT

NO.EA-209-160316

# OUTLINE

R3134x Series are CMOS-based voltage detector ICs with built-in delay circuit, high detector threshold accuracy, and ultra low supply current, which can operate at low voltage.

These ICs can be used as system reset generators, and each of these ICs consists of a voltage reference, a comparator, resistors for setting voltage detector threshold, an output driver transistor, manual reset circuit, and an output delay generator.

Detector threshold is fixed internally with high accuracy and requires no adjustment. When a supply voltage crosses a setting detector threshold voltage from a high value to a lower value, this IC generates reset signal.

R3134x Series output "L" at its detect.

Since each of R3134x Series embeds an output delay generator, during a setting 240ms delay time, which is fixed in the IC, this IC keeps the reset condition after they are released. Released conditions will be kept for the delay time from when a supply voltage crosses a setting detector threshold voltage from a low value to a higher value, or from when the manual reset signal is released.

Two output types, Nch open drain type and CMOS type, are available.

Since the packages for these ICs are DFN(PL)1212-6, SOT-23-5, and SC-88A, high density mounting of the ICs on board is possible.

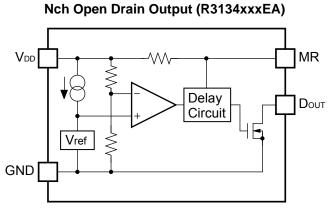
### **FEATURES**

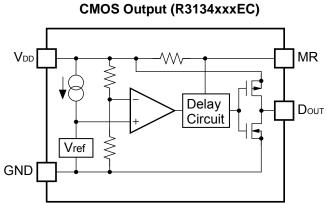
Supply Current	Typ. 0.8μA (R3134x27Ex, Vɒɒ=3.0V)
Operating Voltage Range	0.75V to 6.0V (Topt=25°C)
Detector Threshold Range	1.0V to 5.0V (0.1V steps)
	Further, 2.32V, 2.63V, 2.93V, 3.08V, 4.38V, and
	4.63V can be provided as standard.
Detector Threshold Accuracy	±1.8%
• Temperature-Drift Coefficient of Detector Threshold	Typ. ±100ppm/°C
Built-in Delay Time Circuit	Typ. 240ms
Output Delay Time Accuracy	±15%
Output Types	Nch Open Drain and CMOS
Packages	DFN(PL)1212-6, SC-88A, SOT-23-5

# APPLICATIONS

- CPU and Logic Circuit Reset
- Battery Checker
- Window Comparator
- Wave Shaping Circuit
- Battery Back-up Circuit
- Power Failure Detector

### **BLOCK DIAGRAMS**





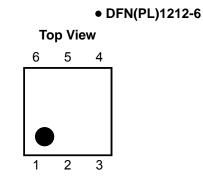
### **SELECTION GUIDE**

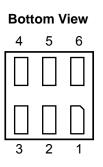
The package type, the detector threshold, the output type and the taping type for the ICs can be selected at the users' request.

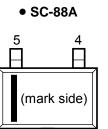
Product Name	Package	Quantity per Reel	Pb Free	Halogen Free	
R3134KxxE*(y)-TR	DFN(PL)1212-6	5,000 pcs	Yes	Yes	
R3134QxxE*(y)-TR-FE	SC-88A	SC-88A 3,000 pcs Yes			
R3134NxxE*(y)-TR-FE	SOT-23-5	3,000 pcs	Yes	Yes	
y: If the detector thresho	d can be designated in the rang old includes the 3rd digit, indica stor threshold is 2.63V, R3134x	te the digit of 0.01V.	5.0V(50) in 0.1'	V steps.	
* : Designation of Output (A) Nch Open Drain	t Туре				

(C) CMOS

### **PIN CONFIGURATIONS**



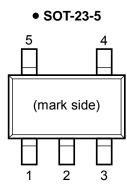




L 2

1

3



### **PIN DESCRIPTIONS**

### • DFN(PL)1212-6

• SC-88A

Pin No.	Symbol	Description	Pin No
1	Vdd	Input Pin	1
2	NC	No Connection	2
3	GND	Ground Pin	3
4	Dout	Output Pin ("L" at detection)	4
5	NC	No Connection	5
6	MR	Manual Reset Input Pin*	

Pin No.	Symbol	Description
1	Vdd	Input Pin
2	GND	Ground Pin
3	MR	Manual Reset Input Pin*
4	Dout	Output Pin ("L" at detection)
5	NC	No Connection

### • SOT-23-5

Pin No.	Symbol	Description
1	Dout	Output Pin ("L" at detection)
2	Vdd	Input Pin
3	GND	Ground Pin
4	MR	Manual Reset Input Pin*
5	NC	No Connection

\*) MR pin is active at "L" input. Pulled up via 1MΩ (Typ.). If MR pin is not necessary, open this node, or connect it to V<sub>DD</sub>.

### Nisshinbo Micro Devices Inc.

### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Item	Rating	Unit
Vdd	Supply Voltage	6.5	V
Vout	Output Voltage (Nch Open Drain Output)	Vss-0.3 to 6.5	V
VOUT	Output Voltage (CMOS Output)	Vss-0.3 to Vdd+0.3	v
Vmr	Input Voltage	Vss-0.3 to Vdd+0.3	V
Іоит	Output Current	20	mA
	Power Dissipation (DFN(PL)1212-6)*	400	
PD	Power Dissipation (SC-88A)*	380	mW
	Power Dissipation (SOT-23-5)*	420	
Topt	Operating Temperature Range	-40 to 85	٥°
Tstg	Storage Temperature Range	–55 to 125	٥C

\*) For Power Dissipation, please refer to PACKAGE INFORMATION.

### ABSOLUTE MAXIMUM RATINGS

Electronic and mechanical stress momentarily exceeded absolute maximum ratings may cause the permanent damages and may degrade the life time and safety for both device and system using the device in the field. The functional operation at or over these absolute maximum ratings is not assured.

# **ELECTRICAL CHARACTERISTICS**

### • R3134x

The specification in \_\_\_\_\_ is checked and guaranteed by design engineering at  $-40^{\circ}C \le T_{opt} \le 85^{\circ}C$ .

Topt=25°C

Symbol	Item	C	onditions	Min.	Тур.	Max.	Unit
Vdet	Detector Threshold			V <sub>DET</sub> ×0.982		V <sub>DET</sub> ×1.018	V
SS1	Supply Current1	VDD=VDET-C	0.1V, Iout=0A			2.0	μA
lss2	Supply Current2	VDD=VDET+0	0.1V, Iout=0A			2.0	μA
			V <sub>DET</sub> < 1.6V			3.6	
Iss3 Supply Current3	Supply Current3	Vdd=6V, Iout=0A	$1.6 \le V_{\text{DET}} < 2.7V$			3.0	μA
		1001-074	$2.7V \le V_{\text{DET}}$			2.5	
		Topt=25°C		0.75		6.00	
V <sub>DD</sub> Operating Voltage	$-40^{\circ}C \le Topt \le 85^{\circ}C$		0.85		6.00	V	
Vон	"H" Output Voltage		Refer to	the followin	g table		
Vol	"L" Output Voltage		Refer to	the followin	g table		
VIH	MR pin "H" Input Voltage	$V_{\text{DD}} \ge V_{\text{DET}}$	⊦0.1V	0.75×V <sub>DD</sub>			V
VIL	MR pin "L" Input Voltage	$V_{DD} \ge V_{DET}$	⊦0.1V			0.2×V <sub>DD</sub>	V
Rmr	MR pin pull-up Resistance	Topt=25°C		0.5	1.0	4.0	MΩ
$\Delta V_{DET}/\Delta T_{opt}$	Detector Threshold Temperature Coefficient	$-40^{\circ}C \le T_{c}$	$opt \leq 85^\circ C$		±100		ppm ∕°C
treset	Output Delay Time for detect *	Vdd=Vdet→ Vdet-0.1V			15		μS
tdelay	Output Delay Time for release	VDD=0.8V-	→ Vdet+1.0	204	240	276	ms

\*) Guaranteed by design, not mass production tested.

### RECOMMENDED OPERATING CONDITIONS (ELECTRICAL CHARACTERISTICS)

All of electronic equipment should be designed that the mounted semiconductor devices operate within the recommended operating conditions. The semiconductor devices cannot operate normally over the recommended operating conditions, even if when they are used over such conditions by momentary electronic noise or surge. And the semiconductor devices may receive serious damage when they continue to operate over the recommended operating conditions.

### • "H" Output Voltage (Vон) table

Topt=25°C

Dreducto	Detector Threshold	"H" Output Voltage Vон (V)						
Products	Vdet (V)	Conditions	Min.	Тур.	Max.			
	V <sub>DET</sub> < 1.2V	VDD=VDET+0.1V, IOH=50 $\mu$ A						
	$1.2V \le V_{\text{DET}} < 2.0V$							
R3134xxxEC	$2.0V \leq V_{\text{DET}} < 3.1V$	Vdd=Vdet+0.1V, Iон=500µA	0.8×Vdd					
	$3.1V \le V_{\text{DET}}$	Vdd=Vdet+0.1V, Iон=800µA						

VDET is a set value.

### • "L" Output Voltage (Vo∟) table

Topt=25°C

Products	Detector Threshold	"L" Output Voltage Vo∟ (V)							
FIDUUCIS	Vdet (V)	Conditions	Min.	Тур.	Max.				
	Vdet < 1.2V	VDD=VDET-0.1V, IOL=200µA			0.04				
	$1.2V \le V_{\text{DET}} < 2.0V$	Vdd=Vdet-0.1V, Iol=750µA			0.06				
R3134xxxEx	$2.0V \leq V_{\text{DET}} < 3.1V$	VDD=VDET-0.1V, IOL=1.2mA			0.05				
	$3.1V \le V_{\text{DET}}$	VDD=VDET-0.1V, IOL=3.2mA			0.06				

VDET is a set value.

# DETECTOR THRESHOLD SPECIFICATIONS BY PART NUMBER

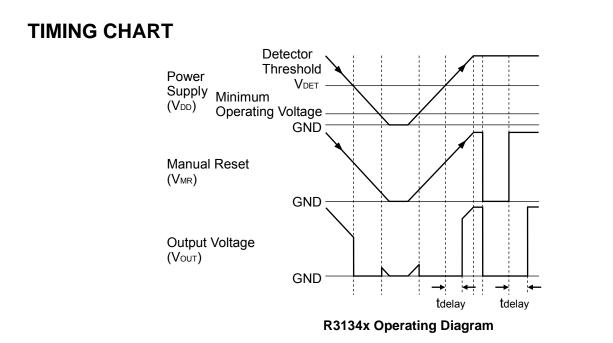
### • R3134x

		Operating Voltage		Detec	tor Thre	shold	Supply Current 1				
Part Number		V	/DD [V]			VDET [V]		Issı [	μΑ]		
	Conditions	Min.	Conditions	Min.	Min.	Тур.	Max.	Conditions	Тур.	Max.	
R3134x23Ex2					2.278	2.320	2.362		0.8		
R3134x26Ex3					2.583	2.630	2.677		0.0		
R3134x29Ex3	Tant 25°C	0.75	$1/5$ $1-40^{\circ}$ $(1 < 100^{\circ} < 85^{\circ} < 10.85^{\circ}$	VDD=VDET-0.1V				2.0			
R3134x30Ex8	Topt=25°C	0.75		0.05	3.025	3.080	3.135	IOUT=0A		2.0	
R3134x43Ex8					4.301	4.380	4.459		0.9		
R3134x46Ex3					4.547	4.630	4.713				
R3134x10Ex					0.982	1.000	1.018				
R3134x11Ex					1.080	1.100	1.120				
R3134x12Ex					1.178	1.200	1.222				
R3134x13Ex					1.277	1.300	1.323				
R3134x14Ex					1.375	1.400	1.425				
R3134x15Ex					1.473	1.500	1.527				
R3134x16Ex					1.571	1.600	1.629				
R3134x17Ex					1.669	1.700	1.731				
R3134x18Ex					1.768	1.800	1.832		0.8		
R3134x19Ex					1.866	1.900	1.934				
R3134x20Ex					1.964	2.000	2.036				
R3134x21Ex					2.062	2.100	2.138				
R3134x22Ex					2.160	2.200	2.240				
R3134x23Ex					2.259	2.300	2.341				
R3134x24Ex					2.357	2.400	2.443				
R3134x25Ex					2.455	2.500	2.545	-			
R3134x26Ex						2.553	2.600	2.647			
R3134x27Ex				2.651 2.700 2.749							
R3134x28Ex	•				2.750	2.800	2.850	-			
R3134x29Ex					2.848	2.900	2.952				
R3134x30Ex	Topt=25°C	0.75 –40°C ≤ Topt ≤ 85°C	0.85	2.946	3.000	3.054	VDD=VDET-0.1V		2.0		
R3134x31Ex	1001-20 0	0.70		0.00	3.044	3.100	3.156	Iout=0A		2.0	
R3134x32Ex					3.142	3.200	3.258				
R3134x33Ex					3.241	3.300	3.359				
R3134x34Ex					3.339	3.400	3.461				
R3134x35Ex					3.437	3.500	3.563				
R3134x36Ex					3.535	3.600	3.665				
R3134x37Ex					3.633	3.700	3.767				
R3134x38Ex					3.732	3.800	3.868				
R3134x39Ex					3.830	3.900	3.970		0.9		
R3134x40Ex					3.928	4.000	4.072				
R3134x41Ex	1				4.026	4.100	4.174				
R3134x42Ex	1				4.124	4.200	4.276				
R3134x43Ex	4				4.223	4.300	4.377				
R3134x44Ex	4				4.321	4.400	4.479				
R3134x45Ex	4				4.419	4.500	4.581				
R3134x46Ex	-	4.517 4.600 4.683									
R3134x47Ex	4				4.615	4.700	4.785				
R3134x48Ex			4.714	4.800	4.886						
R3134x49Ex	4				4.812	4.900	4.988				
R3134x50Ex					4.910	5.000	5.090				

Supply Cu	urrent 2		Supply C	urrent 3	}	"H" Output Vol	tage			
Iss2 [µ	ιA]		Issa		1	Vон [V]	1			
Conditions	Тур.	Max.	Conditions	Тур.	Max.	Conditions	Min.			
Vdd=Vdet+0.1V	0.0	2.0	Vdd=6.0V	1.2	3.0	Vdd=Vdet+0.1V Іон=500µА	0.8×			
Iout=0A	0.8	2.0	Iout=0A	1.0	2.5	Vdd=Vdet+0.1V Іон=800µА	Vdd			
						Vdd=Vdet+0.1V Iон=50µA				
					3.6					
				1.4		Vdd=Vdet+0.1V Іон=150µА				
					3.0					
				1.2		Vdd=Vdet+0.1V Іон=500µА				
VDD=VDET+0.1V	0.8	0.8	0.8	0.8	2.0	VDD=6.0V				0.8×
Iout=0A			Iout=0A	1.0	2.5	Vdd=Vdet+0.1V Іон=800µА	- Vod			
				0.8						

	"L" Output Vo	oltage	MR pin "H" Voltage		MR pin "L" Voltage		MR pin p	ull-up re	esistanc	e					
Part Number	Vo∟[V]	Vo∟[V]			Vı∟[V]		Rmr [ <b>Μ</b> Ω]								
	Conditions	Max.	Conditions	Min.	Conditions	Max.	Conditions	Min.	Тур.	Max.					
R3134x23Ex2															
R3134x26Ex3	VDD=VDET-0.1V	0.05													
R3134x29Ex3	lo∟=1.2mA	IOL=1.2mA	0.05		0.75×	$V_{DD} \ge V_{DET+0.1}$	0.2×	Tant 25%	0.5	1.0	4.0				
R3134x30Ex8			$V\text{DD} \geq V\text{DET} {+} 0.1$	Vdd	VDD≥VDEI+U.I	Vdd	Topt=25°C	0.5	1.0	4.0					
R3134x43Ex8	VDD=VDET-0.1V	0.06													
R3134x46Ex3	IoL=3.2mA	0.00													
R3134x10Ex	VDD=VDET-0.1V	0.04													
R3134x11Ex	IoL=200μA	0.04													
R3134x12Ex															
R3134x13Ex															
R3134x14Ex															
R3134x15Ex	VDD=VDET-0.1V	0.06													
R3134x16Ex	lol=750μA	0.00													
R3134x17Ex															
R3134x18Ex															
R3134x19Ex															
R3134x20Ex															
R3134x21Ex															
R3134x22Ex															
R3134x23Ex		0.05													
R3134x24Ex	VDD=VDET-0.1V														
R3134x25Ex	IOL=1.2mA		0.05	0.05	0.05	0.05	0.05								
R3134x26Ex		IOL= 1.2111A	10L=1.211A												
R3134x27Ex															
R3134x28Ex															
R3134x29Ex					0.75×		0.2.								
R3134x30Ex			$V\text{DD} \geq V\text{DET}{+}0.1$	VDD	$V\text{DD} \geq V\text{DET}{+}0.1$	0.2× VDD	Topt=25°C	0.5	1.0	4.0					
R3134x31Ex				VDD		<b>V</b> 00									
R3134x32Ex															
R3134x33Ex															
R3134x34Ex															
R3134x35Ex															
R3134x36Ex															
R3134x37Ex	1														
R3134x38Ex	1														
R3134x39Ex	1														
R3134x40Ex	VDD=VDET-0.1V	0.06													
R3134x41Ex	IoL=3.2mA	0.00													
R3134x42Ex	1														
R3134x43Ex	1														
R3134x44Ex															
R3134x45Ex															
R3134x46Ex															
R3134x47Ex															
R3134x48Ex															
R3134x49Ex	]														
R3134x50Ex															

Output Delay Time for Release				Detector Threshold Temperature Coefficient	
tdelay [ms]				ΔVDET/ΔTopt [ppm/°C]	
Conditions	Min.	Тур.	Max.	Conditions	Тур.
VDD=0.8V→ VDET+1.0V Topt=25°C	204	240	276	–40°C ≤ Topt ≤ 85°C	±100
VDD=0.8V→ VDET+1.0V Topt=25°C	204	240	276	-40°C ≤ Topt ≤ 85°C	±100



### **DEFINITION OF OUTPUT DELAY TIME**

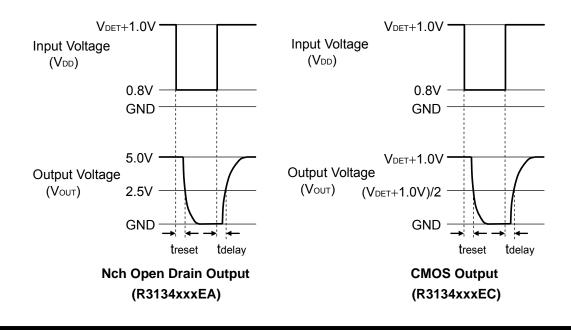
Output Delay Time (tdelay) is specified as follows:

1. In the case of Nch Open Drain Output:

The time interval from rising edge of  $V_{DD}$  pulse 0.8V to  $V_{DET}$ +1.0V to the time at which the output reaches 2.5V under the condition that the output pin (D<sub>OUT</sub>) is pulled up to 5V through a 470k $\Omega$  resistor.

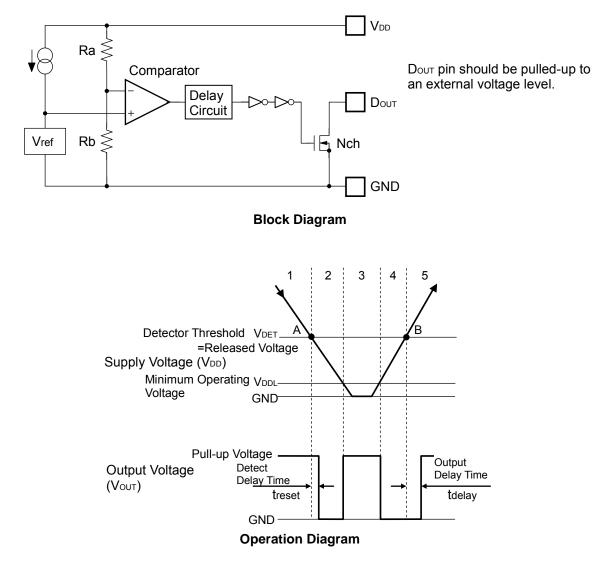
2. In the case of CMOS Output:

The time interval from rising edge of  $V_{DD}$  pulse 0.8V to  $V_{DET}$ +1.0V to the time at the output reaches ( $V_{DET}$ +1.0V)/2.



### **OPERATION**

Operation of R3134xxxEA

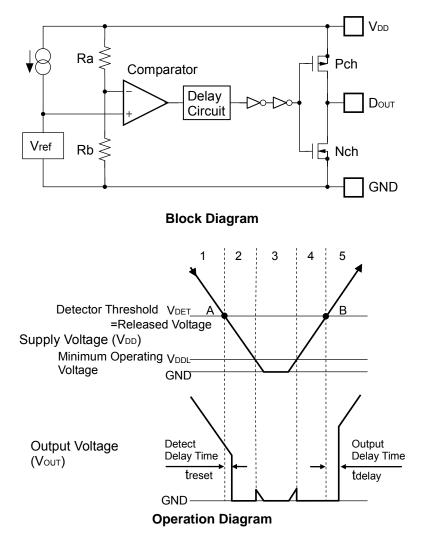


#### Explanation of operation

Step 1. The output voltage is equal to the pull-up voltage.

- Step 2. At Point "A", Vref ≥ V<sub>DD</sub>×Rb/(Ra+Rb) is true, as a result, the output of comparator is reversed from "L" to "H", therefore the output voltage becomes the GND level. The voltage level of Point A means a detector threshold voltage (V<sub>DET</sub>).
- Step 3. When the supply voltage is lower than the minimum operating voltage, the operation of the output transistor becomes indefinite. The output voltage is equal to the pull-up voltage.
- Step 4. The output voltage is equal to the GND level.
- Step 5. At Point "B", Vref ≤ V<sub>DD</sub>×Rb/(Ra+Rb) is true, as a result, the output of comparator is reversed from "H" to "L", then the output voltage is equal to the pull-up voltage. The voltage level of Point B means a released voltage (V<sub>DET</sub>).
- \*) There is no hysteresis range between the detector threshold and the released voltage.

#### Operation of R3134xxxEC



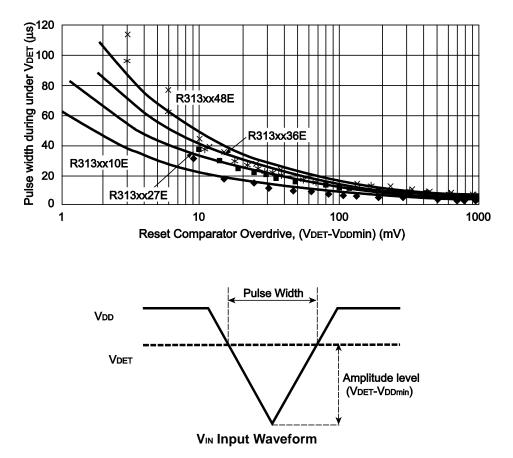
#### • Explanation of operation

Step 1. The output voltage is equal to the supply voltage ( $V_{DD}$ ).

- Step 2. At Point "A", Vref ≥ V<sub>DD</sub>×Rb/(Ra+Rb) is true, as a result, the output of comparator is reversed from "L" to "H", therefore the output voltage becomes the GND level. The voltage level of Point A means a detector threshold voltage (V<sub>DET</sub>).
- Step 3. When the supply voltage is lower than the minimum operating voltage, the operation of the output transistor becomes indefinite.
- Step 4. The output voltage is equal to the GND level.
- Step 5. At Point "B", Vref ≤ V<sub>DD</sub>×Rb/(Ra+Rb) is true, as a result, the output of comparator is reversed from "H" to "L", then the output voltage is equal to the supply voltage (V<sub>DD</sub>). The voltage level of Point B means a released voltage (V<sub>DET</sub>).
- \*) There is no hysteresis range between the detector threshold and the released voltage.

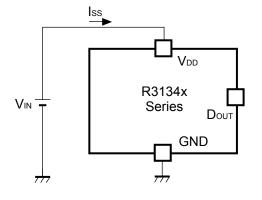
### Detector Operation vs. glitch input voltage to the VDD pin

When the IC is released and a large pulse (glitch) crosses the detector threshold is forced, the IC may not maintain the released condition. The amplitude of the pulse (V<sub>DET</sub>-V<sub>DD</sub>min) and the pulse width the IC can maintain the released level is described in the graph as follows:

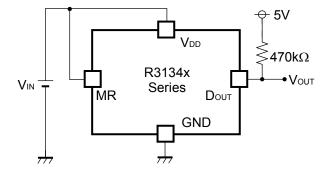


The graph above shows the condition for the maximum transient duration without generating a reset. If the larger amplitude or larger pulse width noise than the graph may be on the  $V_{DD}$ , the reset signal may be generated.

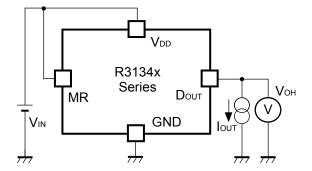
# **TEST CIRCUITS**



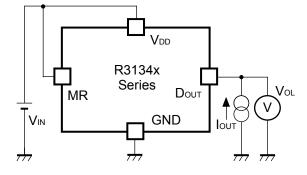
**Supply Current Test Circuit** 



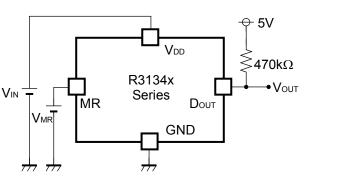
Detector Threshold Test Circuit (Pull-up circuit is not necessary for CMOS Output type.)



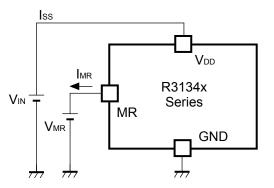
"H" Output Voltage Test Circuit (CMOS Output Type only)



"L" Output Voltage Test Circuit



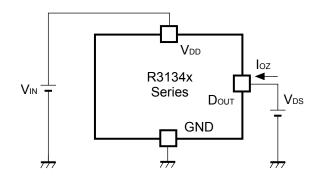
MR pin Input Voltage Test Circuit (Pull-up circuit is not necessary for CMOS Output type.)



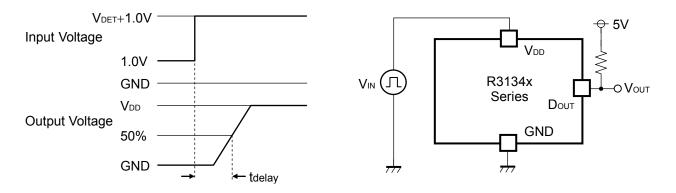


\* R3134K (DFN(PL)1212-6) and R3134Q (SC-88A) are the discontinued products as of March, 2016.

### R3134x



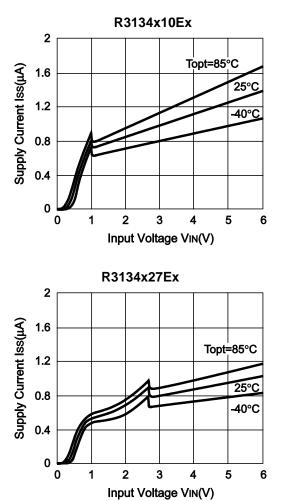
**Off Leakage Current Test Circuit** 



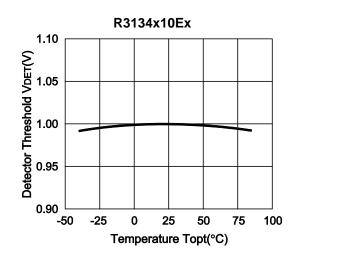
Output Delay Time Test Circuit (Pull-up circuit is not necessary for CMOS Output type.)

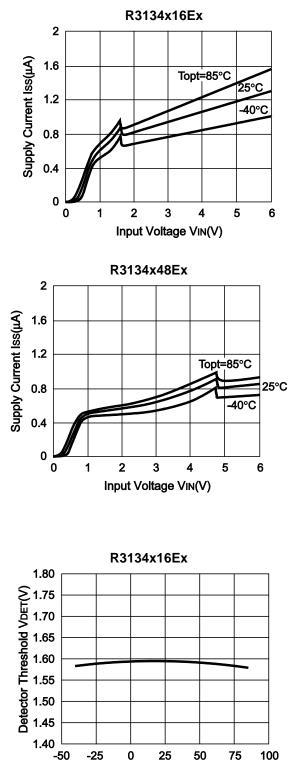
# **TYPICAL CHARACTERISTICS**

1) Supply Current vs. Input Voltage



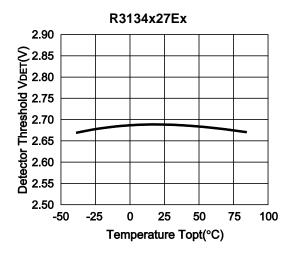


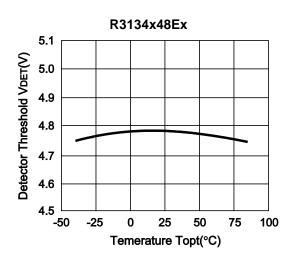




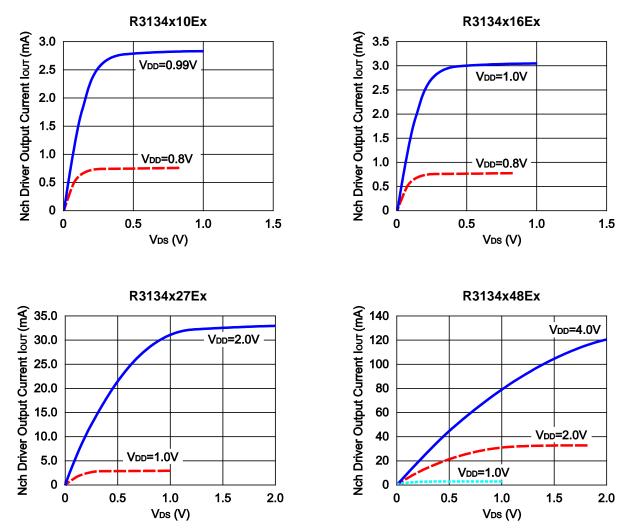
Temperature Topt(°C)



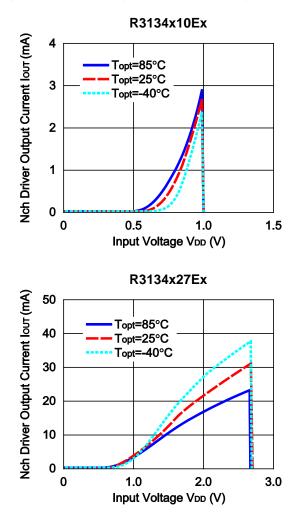




### 3) Nch Driver Output Current vs. VDs (Topt=25°C)

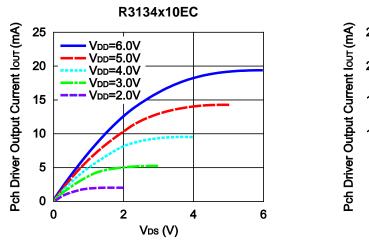


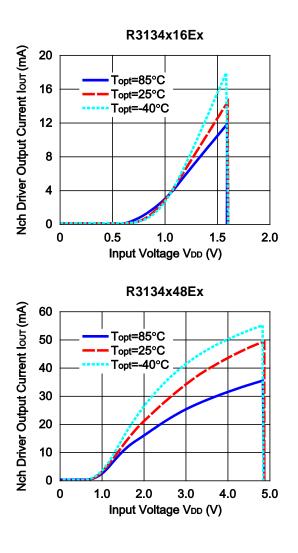
Nisshinbo Micro Devices Inc.

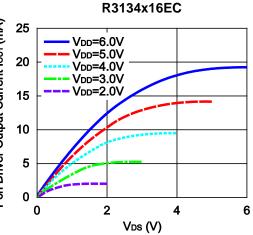


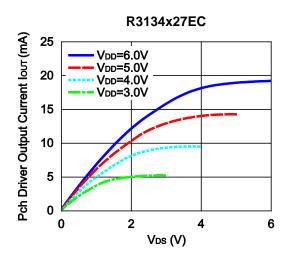
#### 4) Nch Driver Output Current vs. Input Voltage

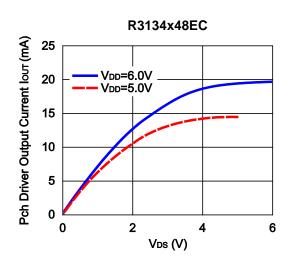




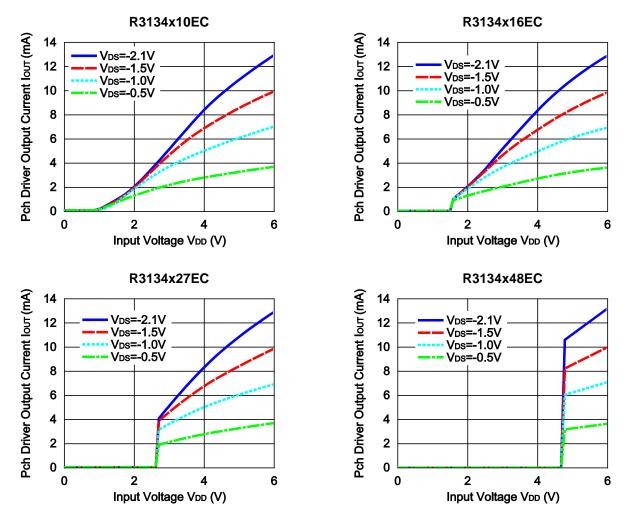




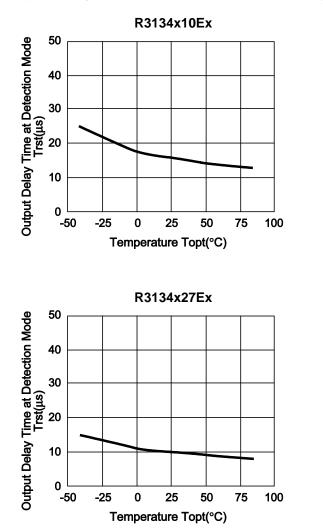




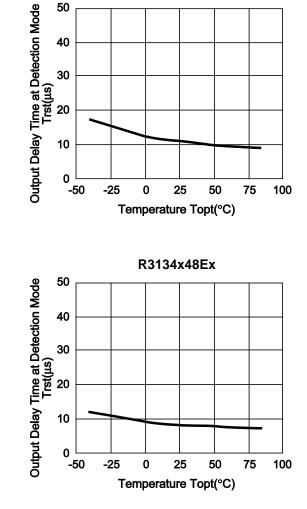
### 6) Pch Driver Output Current vs. Input Voltage



### Nisshinbo Micro Devices Inc.



### 7) Output Delay Time at Detection Mode vs. Temperature

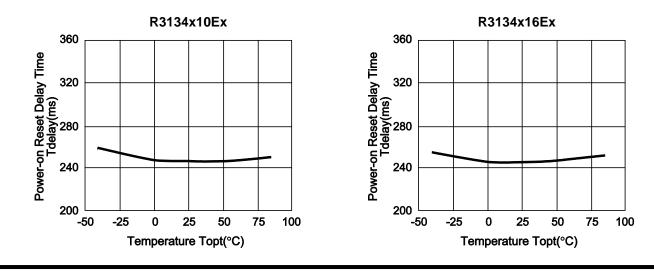


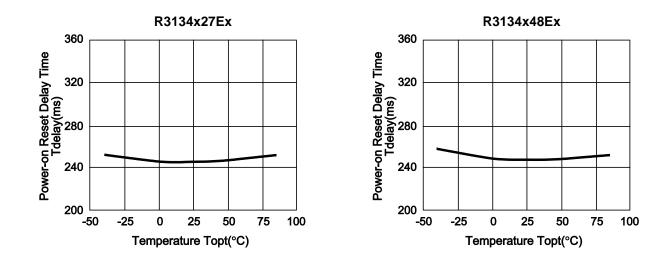
R3134x16Ex

50

40







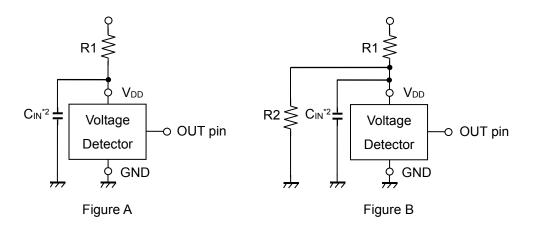
### **TECHNICAL NOTES**

### When connecting resistors to the device's input pin

When connecting a resistor (R1) to an input of this device, the input voltage decreases by [Device's Consumption Current] x [Resistance Value] only. And, the cross conduction current\*1, which occurs when changing from the detecting state to the release state, is decreased the input voltage by [Cross Conduction Current] x [Resistance Value] only. And then, this device will enter the re-detecting state if the input voltage reduction is larger than the difference between the detector voltage and the released voltage.

When the input resistance value is large and the VDD is gone up at mildly in the vicinity of the released voltage, repeating the above operation may result in the occurrence of output.

As shown in Figure A/B, set R1 to become 100 k $\Omega$  or less as a guide, and connect C<sub>IN</sub> of 0.1  $\mu$ F and more to between the input pin and GND. Besides, make evaluations including temperature properties under the actual usage condition, with using the evaluation board like this way. As a result, make sure that the cross conduction current has no problem.



\*<sup>1</sup> In the CMOS output type, a charging current for OUT pin is included.

\*<sup>2</sup> Note the bias dependence of capacitors.

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